查询PF0015供应商 捷多邦,专业PCB打样工厂,24小时 MOS FET Power Amplifier Module for Handy Mobile Phone 地名山地

加急出货

MOS FET Power Amplifier FOR AMPS 824 ~ 849 MHz

## **■ FEATURES**

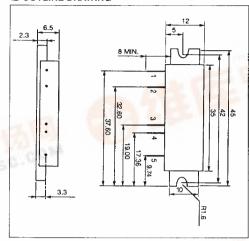
- Small outline  $12 \times 45 \times 6.5 \text{ mm}^3$
- · Low voltage operation 6V
- Low power control current 300 μA
- High stability load VSWR ≥ 20

## ■ ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Item	Symbol	Rating	Unit
Supply Voltage	$V_{\mathrm{DD}}$	12	V
Supply Current	$I_{\mathrm{DD}}$	2	Α
APC Voltage	VAPC	± 8	V
Input Power	Pin	20	mW
Operating Case Temperature	T <sub>C(op)</sub>	-30 ~ + 100	°C
Storage Temperature	T <sub>stg</sub>	-30 ~ + 100	°C

The absolute maximum ratings are limiting values, to be applied individually, beyond which the device may be permanently damaged. Functional operation under any of these conditions is not guaranteed. Exposing a circuit to its absolute maximum rating for extended periods of time may affect the device's reliability.

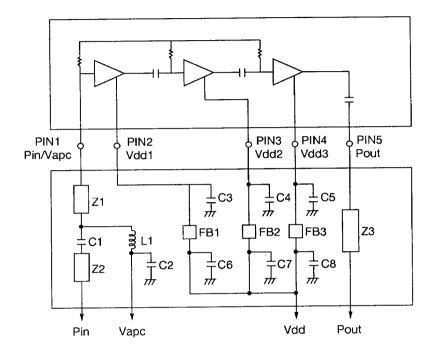
## OUTLINE DRAWING



## ■ ELECTRICAL CHARACTERISTICS (Ta =

Symbol	Test Condition	min.	typ.	max.	Unit
I <sub>DS</sub>	$V_{DD1} = V_{DD2} = V_{DD3} = 12V, V_{apc} = 0V$	_	_	100	μΑ
$\eta_{\mathrm{T}}$	$ f = 824, 849 \text{ MHz}, \\ P_{in} = 1 \text{ mW}, \\ V_{DD1} = V_{DD2} = V_{DD3} = 6V, \\ P_{out} = 1.2W \text{ (at APC Control)}, \\ Z_{in} = Z_{out} = 50 \Omega $	35	40	_	%
2nd H.D.		_	-40	-30	dB
3rd H.D.		_	-50	-30	dB
VSWR(in)		_	1.8	3	_
VSWR(out)		_	2		_
_	$\begin{array}{c} V_{DD1} = V_{DD2} = V_{DD3} = 6\text{V},  P_{in} = 1  \text{mW}, \\ f = 824  \text{MHz},  R_g = 50  \Omega, \\ P_{out} = 1.2\text{W}   (\text{at APC Control}), \\ Output  \text{VSWR} = 20  \text{All Phases},  t = 20  \text{sec} \end{array}$	No Parastic Oscillation			
	l <sub>DS</sub> ηT  2nd H.D.  3rd H.D.  VSWR(in)	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

#### **■ TEST SYSTEM DIAGRAM**



 $C_1 = 0.02 \mu F$  Ceramic Chip

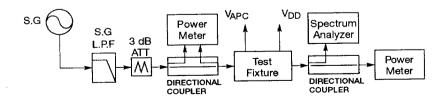
 $C_2$ ,  $C_3$ ,  $C_4$ ,  $C_5 = 0.01 \mu F$  Ceramic Dip

 $C_6$ ,  $C_7$ ,  $C_8 = 10 \mu F$  Tantalum

 $L_1 = RFC 1mm \phi$ , 15 turns

FB = Ferrite Bead BL01RN1-A62-001 (MURATA) or equivalent

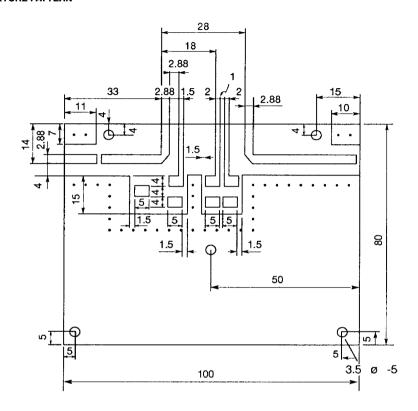
 $Z_1$ ,  $Z_2$ ,  $Z_3 = 50 \Omega$  Microstrip Line



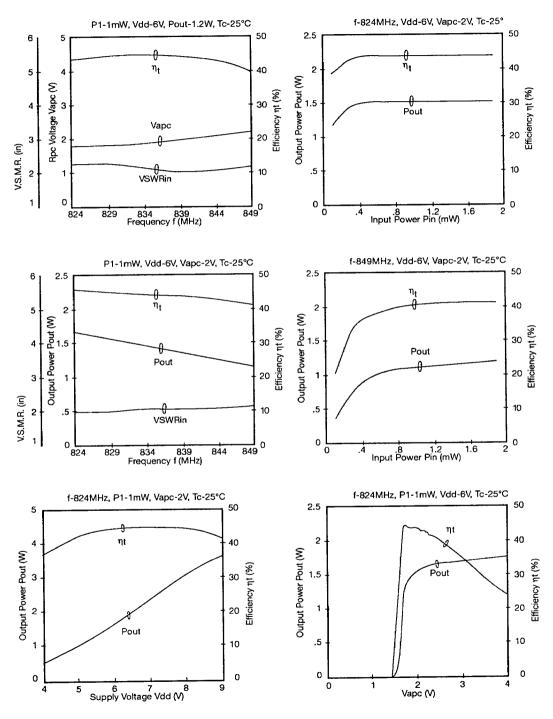
Output power P<sub>out</sub> is defined at the root point of the module output pin P<sub>out</sub>. The coefficient of output power loss in the PCB output line Z3 is shown below.

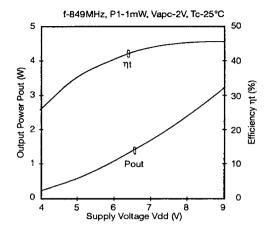
$$1/S_{21})^2 = 1/(0.9805)^2 = 1.04$$

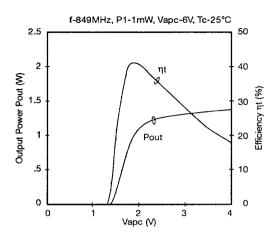
# **■ TEST FIXTURE PATTERN**



Grass Epoxy Double Sided PCB ( $t = 1.6 \text{ mm}, \epsilon r = 4.8$ )







### • Mechanical Characteristics

Item	Conditions	Spec.	
Torque for screw up the heatsink flange	M3 Screw-Bolts	4 ~ 6 kg/cm	
Warp size of the heatsink flange: S	minimum mumimum.	S = O +0.3/-0 mm	

#### **Note for Use**

- 1. Unevenness and distortion at the surface of the heatsink attached PF0015 should be less than 0.05 mm.
- 2. It should not be existed any dust between PF0015 and heatsink.
- 3. PF0015 should be separated from PCB more than 1.5 mm.
- 4. Soldering temperature and soldering time should be less than 230°C, 10 sec. (Soldering position spaced from the root point of the lead frame: 2 mm).
- 5. Recommendation of thermal joint compounds is TYPE G746 (Manufacturer: Shin-Etu Chemical, Co., Ltd.) or equivalent.
- 6. To protect devices from electro-static damage, soldering iron, measuring-equipment and human body etc. should be grounded.